



### **IRF7807ZTRPBF Information**



For Reference Only

Part Number IRF7807ZTRPBF
Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description**MOSFET N-CH 30V 11A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **IRF7807ZTRPBF Specifications**

Manufacturer Part NumberIRF7807ZTRPBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackage8-SOIC (0.154", 3.90mm Width)SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C11A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.25V @ 250μAGate Charge (Qg) (Max) @ Vgs11nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds770pF @ 15VVgs (Max)±20VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs13.8 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         8-SOIC (0.154", 3.90mm Width)           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         30V           Current - Continuous Drain (Id) @ 25°C         11A (Ta)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.25V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         11nC @ 4.5V           Input Capacitance (Ciss) (Max) @ Vds         770pF @ 15V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         2.5W (Ta)           Rds On (Max) @ Id, Vgs         13.8 mohm @ 11A, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Surface Mount           Supplier Device Package         8-SO           Package / Case         8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	IRF7807ZTRPBF
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Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Insurance (Tiss) (Max)  Poperating Temperature  Supplier Device Package  Package / Case  4.5V, 10V  2.25V @ 250μA  11nC @ 4.5V  770pF @ 15V  770pF @ 15V  4.5V  770pF @ 15V  770pF @ 15	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  770pF @ 15V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  13.8 mOhm @ 11A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	11A (Ta)
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Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  ET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  13.8 mOhm @ 11A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  Package / Case  8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	2.25V @ 250μA
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Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  13.8 mOhm @ 11A, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-SO  Package / Case  8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±20V
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Surface Mount  Supplier Device Package  8-SO  Package / Case  8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount  Supplier Device Package 8-SO  Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	13.8 mOhm @ 11A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

#### **IRF7807ZTRPBF** Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRF7807ZTRPBF Payment Methods**



















## **IRF7807ZTRPBF Shipping Methods**













If you have any question about IRF7807ZTRPBF, please do not hesitate to contact us!

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